

## TLV354x 200MHz、レール・ツー・レールI/O、 コスト制限の厳しいシステム向けのCMOSオペアンプ

### 1 特長

- 低コストのシステム用の広帯域アンプ
- ユニティ・ゲイン帯域幅: 200MHz
- 高いスルー・レート: 150V/ $\mu$ s
- 低ノイズ: 7.5nV/ $\sqrt{\text{Hz}}$
- レール・ツー・レールI/O
- 高い出力電流: 100mA超
- 非常に優れたビデオ性能
  - 差動ゲイン: 0.02%、差動位相: 0.09°
  - 0.1dBのゲイン・フラットネス(40MHz)
- 低い入力バイアス電流: 3pA
- 静止電流: 5.2mA
- サーマル・シャットダウン
- 電源電圧範囲: 2.5V~5.5V

### 2 アプリケーション

- 高分解能のADCドライバ・アンプ
- IRタッチ
- 低電圧、高周波数の信号処理
- ビデオ処理
- トランシーバ基地局
- 光ネットワーク、調節可能なレーザー
- フォトダイオード・トランスインピーダンス・アンプ
- バーコード・スキャナ
- 高速電流センス・アンプ
- 超音波イメージング

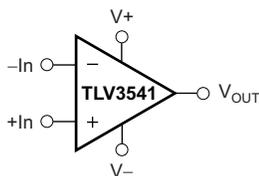


図 1. 概略回路図

### 3 概要

TLV3541、TLV3542、TLV3544はシングル、デュアル、クワッド・チャンネルで低消費電力(チャンネルごとに5.2mA)、高速、ユニティ・ゲイン安定、レール・ツー・レール入力/出力のオペアンプであり、広い帯域幅を必要とするビデオやその他のアプリケーション用に設計されています。

これらのデバイスは、電源からわずか6.5mA (最大値)の電流しか消費せず、200MHzのゲイン帯域幅積、150V/ $\mu$ sのスルー・レート、および $f = 1\text{MHz}$ において7.5 nV/ $\sqrt{\text{Hz}}$ の低い入力ノイズを実現しています。高帯域幅、高いスルー・レート、低いノイズを併せ持つため、TLV354xファミリは低電圧、高速の信号コンディショニング・システムに適しています。

TLV354xシリーズのオペアンプは、最低2.5V ( $\pm 1.25\text{V}$ )、最高5.5V ( $\pm 2.75\text{V}$ )のシングルまたはデュアル電源で動作するよう最適化されています。同相入力範囲は電源の範囲よりも拡大されています。出力スイングはレールから100mV以内で、広いダイナミックレンジに対応しています。

TLV354xデバイスは、 $-40^{\circ}\text{C} \sim +125^{\circ}\text{C}$ での動作が規定されています。TLV354xファミリは、市販されている多くの広帯域オペアンプのプラグイン代替品として使用できます。

#### 製品情報<sup>(1)</sup>

型番	パッケージ	本体サイズ(公称)
TLV3541	SOIC (8)	3.91mm×4.90mm
	SOT-23 (5)	2.90mm×1.60mm
TLV3542	SOIC (8)	3.91mm×4.90mm
	VSSOP (8)	3.00mm×3.00mm
TLV3544	SOIC (14)	8.65mm×3.91mm
	TSSOP (14)	5.00mm×4.40mm

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

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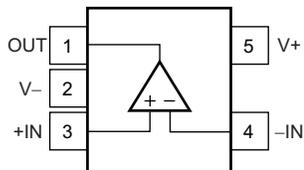
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## 4 改訂履歴

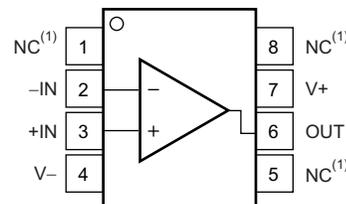
日付	改訂内容	注
2016年10月	*	初版

## 5 Pin Configuration and Functions

**TLV3541: DBV Package  
5-Pin SOT-23  
Top View**



**TLV3541: D Package  
8-Pin SOIC  
Top View**

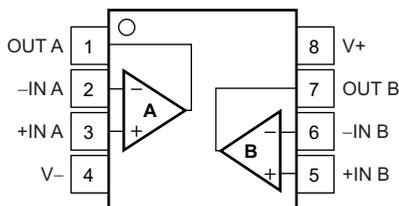


(1) NC means no internal connection.

**Pin Functions: TLV3541**

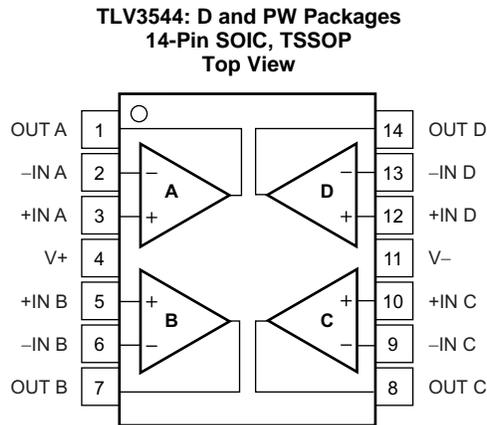
NAME	PIN		I/O	DESCRIPTION
	DBV (SOT-23)	D (SOIC)		
-IN	4	2	I	Inverting input
+IN	3	3	I	Noninverting input
NC	—	1, 5, 8	—	No internal connection (can be left floating)
OUT	1	6	O	Output
V-	2	4	—	Negative (lowest) supply
V+	5	7	—	Positive (highest) supply

**TLV3542: DGK and D Packages  
8-Pin VSSOP, SOIC  
Top View**



**Pin Functions: TLV3542**

NAME	PIN		I/O	DESCRIPTION
	NO.			
-IN A	2		I	Inverting input, channel A
+IN A	3		I	Noninverting input, channel A
-IN B	6		I	Inverting input, channel B
+IN B	5		I	Noninverting input, channel B
OUT A	1		O	Output, channel A
OUT B	7		O	Output, channel B
V-	4		—	Negative (lowest) supply
V+	8		—	Positive (highest) supply


**Pin Functions: TLV3544**

NAME	PIN		I/O	DESCRIPTION
	TLV3544			
	D (SOIC)	PW (TSSOP)		
-IN A	2	2	I	Inverting input, channel A
-IN B	6	6	I	Inverting input, channel B
-IN C	9	9	I	Inverting input, channel C
-IN D	13	13	I	Inverting input, channel D
+IN A	3	3	I	Noninverting input, channel A
+IN B	5	5	I	Noninverting input, channel B
+IN C	10	10	I	Noninverting input, channel C
+IN D	12	12	I	Noninverting input, channel D
OUT A	1	1	O	Output, channel A
OUT B	7	7	O	Output, channel B
OUT C	8	8	O	Output, channel C
OUT D	14	14	O	Output, channel D
V-	11	11	—	Negative (lowest) supply
V+	4	4	—	Positive (highest) supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	Supply voltage, V+ to V-		7.5	V
	Signal input terminals <sup>(2)</sup>	(V-) - (0.5)	(V+) + 0.5	V
Current	Signal input terminals <sup>(2)</sup>	-10	10	mA
	Output short circuit <sup>(3)</sup>	Continuous		
Temperature	Operating, T <sub>A</sub>	-55	150	°C
	Junction, T <sub>J</sub>	-65	150	°C
	Storage, T <sub>stg</sub>		150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	1000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	250	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>S</sub>	Supply voltage, V- to V+	2.5		5.5	V
	Specified temperature range	-40		125	°C

#### 6.4 Thermal Information: TLV3541

THERMAL METRIC <sup>(1)</sup>		TLV3541		UNIT
		D (SOIC)	DBV (SOT-23)	
		8 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	123.8	216.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	68.7	84.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	64.5	43.1	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	23.0	3.8	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	64.0	42.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#) (SPRA953).

#### 6.5 Thermal Information: TLV3542

THERMAL METRIC <sup>(1)</sup>		TLV3542		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	113.9	175.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	60.4	67.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.1	97.1	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	17.1	9.3	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	53.6	95.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#) (SPRA953).

#### 6.6 Thermal Information: TLV3544

THERMAL METRIC <sup>(1)</sup>		TLV3544		UNIT
		D (SOIC)	PW (TSSOP)	
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	83.8	92.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	70.7	27.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	59.5	33.6	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	11.6	1.9	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	37.7	33.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#) (SPRA953).

## 6.7 Electrical Characteristics: $V_S = 2.7\text{ V to }5.5\text{ V}$ Single-Supply

at  $T_A = 25^\circ\text{C}$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFFSET VOLTAGE</b>						
$V_{OS}$	Input offset voltage	$V_S = 5\text{ V}$ , at $T_A = 25^\circ\text{C}$		$\pm 2$	$\pm 10$	mV
$dV_{OS}/dT$	Input offset voltage vs temperature	$V_S = 5\text{ V}$ , at $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		$\pm 4.5$		$\mu\text{V}/^\circ\text{C}$
PSRR	Input offset voltage vs power supply	$V_S = 2.7\text{ V to }5.5\text{ V}$ , $V_{CM} = (V_S / 2) - 0.55\text{ V}$	60	70		dB
<b>INPUT BIAS CURRENT</b>						
$I_B$	Input bias current			3		pA
$I_{OS}$	Input offset current			$\pm 1$		pA
<b>NOISE</b>						
$e_n$	Input voltage noise density	$f = 1\text{ MHz}$		7.5		$\text{nV}/\sqrt{\text{Hz}}$
$i_n$	Current noise density	$f = 1\text{ MHz}$		50		$\text{fA}/\sqrt{\text{Hz}}$
<b>INPUT VOLTAGE RANGE</b>						
$V_{CM}$	Common-mode voltage range		$(V_-) - 0.1$		$(V_+) + 0.1$	V
CMRR	Common-mode rejection ratio	$V_S = 5.5\text{ V}$ , $-0.1\text{ V} < V_{CM} < 3.5\text{ V}$ , at $T_A = 25^\circ\text{C}$	66	80		dB
		$V_S = 5.5\text{ V}$ , $-0.1\text{ V} < V_{CM} < 5.6\text{ V}$ , at $T_A = 25^\circ\text{C}$	56	68		dB
<b>INPUT IMPEDANCE</b>						
	Differential			$10^{13} \parallel 2$		$\Omega \parallel \text{pF}$
	Common-mode			$10^{13} \parallel 2$		$\Omega \parallel \text{pF}$
<b>OPEN-LOOP GAIN</b>						
$A_{OL}$	Open-loop gain	$V_S = 5\text{ V}$ , $0.3\text{ V} < V_O < 4.7\text{ V}$ , at $T_A = 25^\circ\text{C}$	92	108		dB
<b>FREQUENCY RESPONSE</b>						
$f_{-3\text{dB}}$	Small-signal bandwidth	At $G = +1$ , $V_O = 10\text{ mV}$ $R_F = 25\ \Omega$		200		MHz
		At $G = +2$ , $V_O = 10\text{ mV}$		90		MHz
GBW	Gain-bandwidth product	$G = +10$		100		MHz
$f_{0.1\text{dB}}$	Bandwidth for 0.1-dB gain flatness	At $G = +2$ , $V_O = 10\text{ mV}$		40		MHz
SR	Slew rate	$V_S = 5\text{ V}$ , $G = +1$ , 4-V step		150		$\text{V} / \mu\text{s}$
		$V_S = 5\text{ V}$ , $G = +1$ , 2-V step		130		$\text{V} / \mu\text{s}$
	Rise-and-fall time	At $G = +1$ , $V_O = 200\text{ mV}_{PP}$ , 10% to 90%		2		ns
		At $G = +1$ , $V_O = 2\text{ V}_{PP}$ , 10% to 90%		11		ns
	Settling time	0.1%, $V_S = 5\text{ V}$ , $G = +1$ , 2-V output step		30		ns
		0.01%, $V_S = 5\text{ V}$ , $G = +1$ , 2-V output step		60		ns
	Overload recovery time	$V_{IN} \times \text{Gain} = V_S$		5		ns

**Electrical Characteristics:  $V_S = 2.7\text{ V}$  to  $5.5\text{ V}$  Single-Supply (continued)**

 at  $T_A = 25^\circ\text{C}$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>FREQUENCY RESPONSE, continued</b>						
Harmonic distortion	Second harmonic	At $G = +1$ , $f = 1\ \text{MHz}$ , $V_O = 2\ V_{PP}$ , $R_L = 200\ \Omega$ , $V_{CM} = 1.5\ \text{V}$		-75		dBc
	Third harmonic	At $G = +1$ , $f = 1\ \text{MHz}$ , $V_O = 2\ V_{PP}$ , $R_L = 200\ \Omega$ , $V_{CM} = 1.5\ \text{V}$		-83		dBc
Differential gain error		NTSC, $R_L = 150\ \Omega$		0.02%		
Differential phase error		NTSC, $R_L = 150\ \Omega$		0.09		°
Channel-to-channel crosstalk	TLV3542	$f = 5\ \text{MHz}$		-100		dB
	TLV3544			-84		dB
<b>OUTPUT</b>						
Voltage output swing from rail		$V_S = 5\ \text{V}$ , $R_L = 1\ \text{k}\Omega$ at $T_A = 25^\circ\text{C}$		0.1	0.3	V
$I_O$	Output current, single, dual, quad <sup>(1)(2)</sup>	$V_S = 5\ \text{V}$	100			mA
		$V_S = 3\ \text{V}$		50		mA
Closed-loop output impedance		$f < 100\ \text{kHz}$		0.05		$\Omega$
$R_O$	Open-loop output resistance			35		$\Omega$
<b>POWER SUPPLY</b>						
$V_S$	Specified voltage range		2.7		5.5	V
	Operating voltage range		2.5		5.5	V
$I_Q$	Quiescent current (per amplifier)	At $T_A = 25^\circ\text{C}$ , $V_S = 5\ \text{V}$ , $I_O = 0$		5.2	6.5	mA
<b>TEMPERATURE RANGE</b>						
Specified range			-40		125	°C
Operating range <sup>(3)</sup>			-55		150	°C
Storage range			-65		150	°C
<b>THERMAL SHUTDOWN</b>						
Shutdown temperature				160		°C
Reset from shutdown				140		°C

 (1) See typical characteristic curves, *Output Voltage Swing vs Output Current* ( [Fig 14](#) and [Fig 15](#) ).

(2) Specified by design.

(3) Operating in this temperature range will not damage the part. However, degraded performance may be observed.

### 6.8 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $G = +1$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$ , unless otherwise noted.

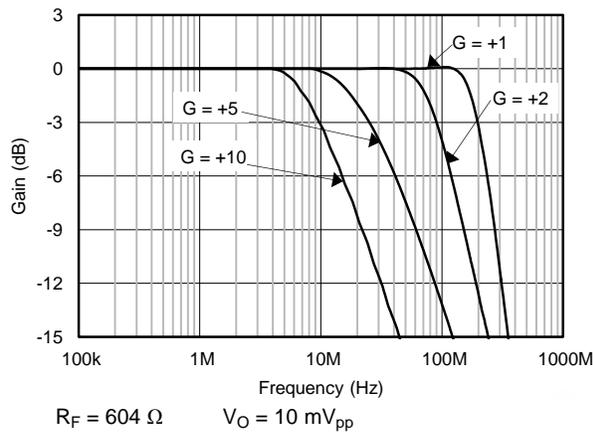


Figure 2. Noninverting Small-Signal Frequency Response

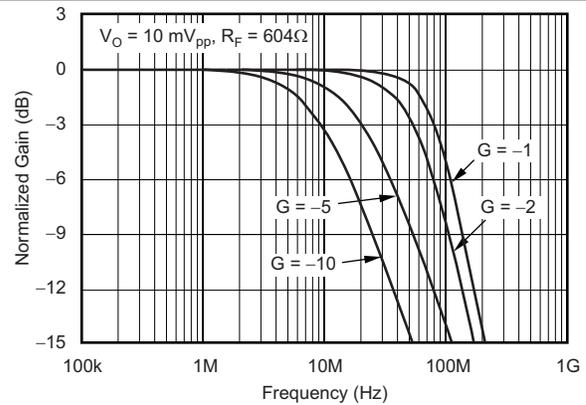


Figure 3. Inverting Small-Signal Frequency Response

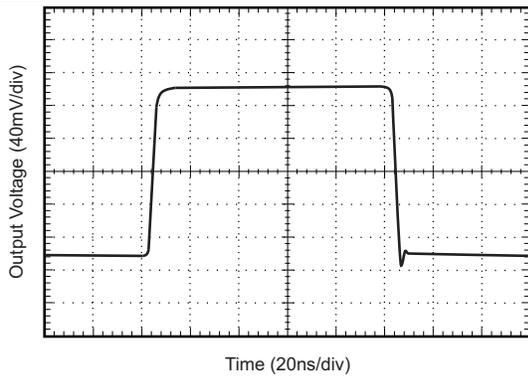


Figure 4. Noninverting Small-Signal Step Response

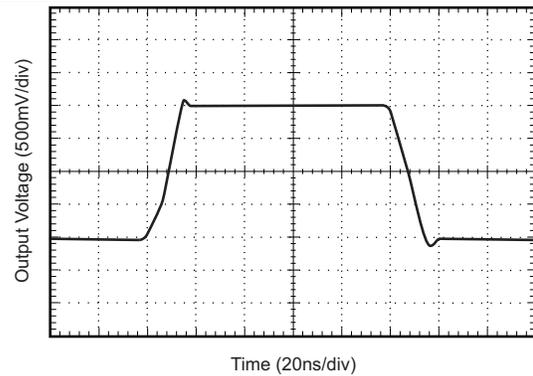


Figure 5. Noninverting Large-Signal Step Response

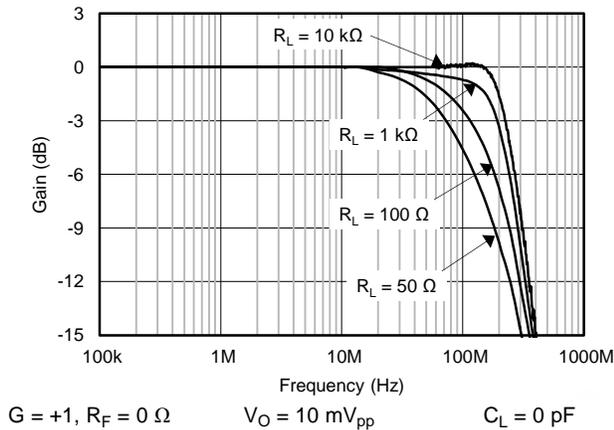


Figure 6. Frequency Response for Various  $R_L$

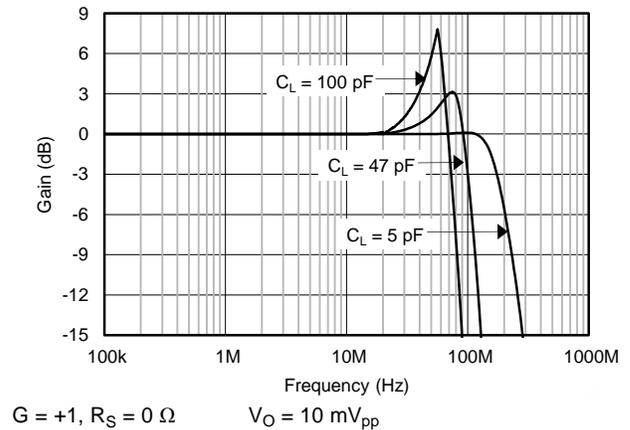
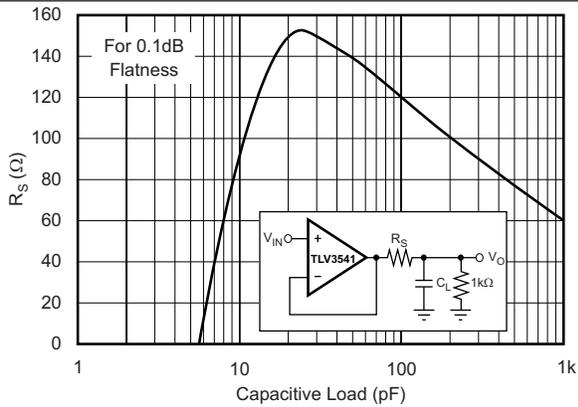


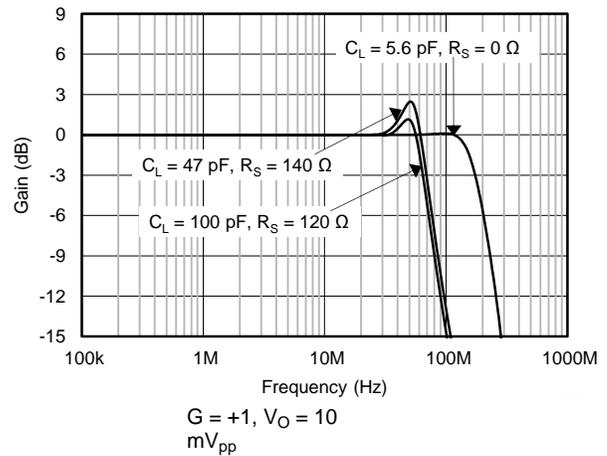
Figure 7. Frequency Response for Various  $C_L$

**Typical Characteristics (continued)**

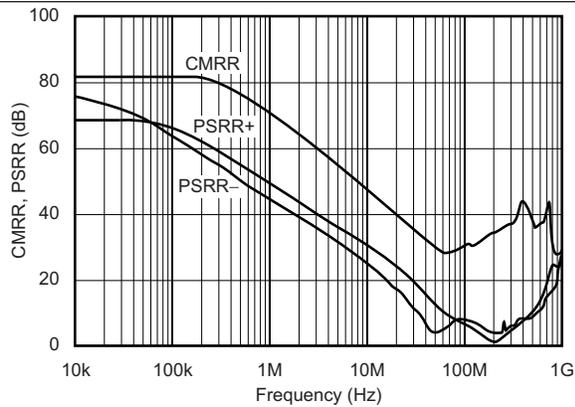
at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $G = +1$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$ , unless otherwise noted.



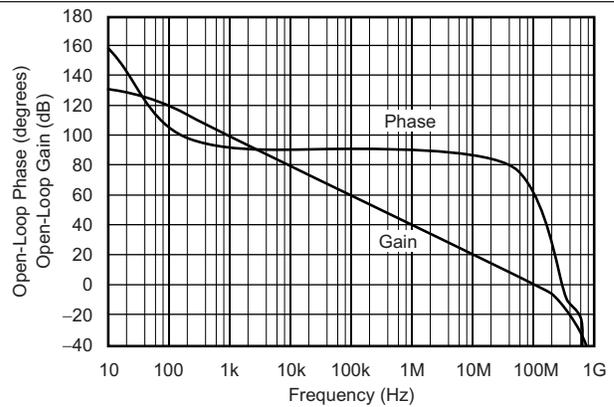
**Fig 8. Recommended  $R_S$  vs Capacitive Load**



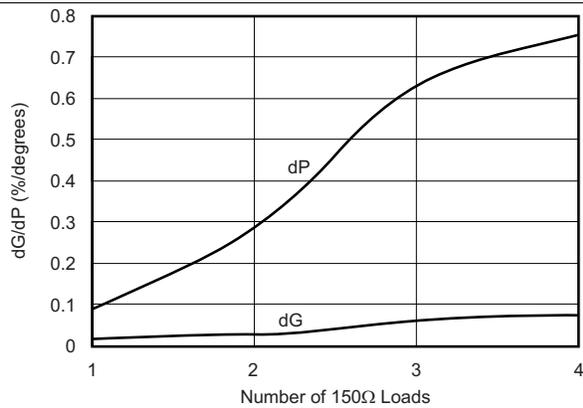
**Fig 9. Frequency Response vs Capacitive Load**



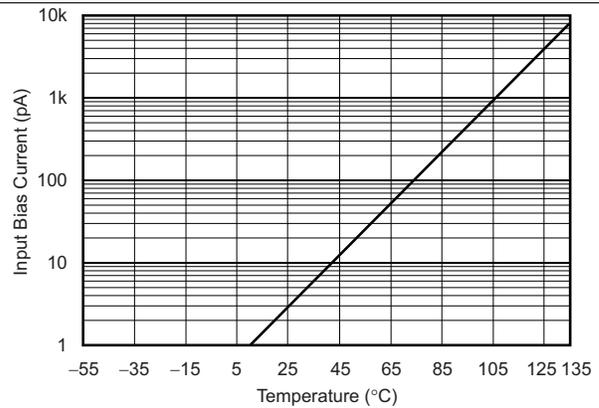
**Fig 10. Common-Mode Rejection Ratio and Power-Supply Rejection Ratio vs Frequency**



**Fig 11. Open-Loop Gain and Phase**



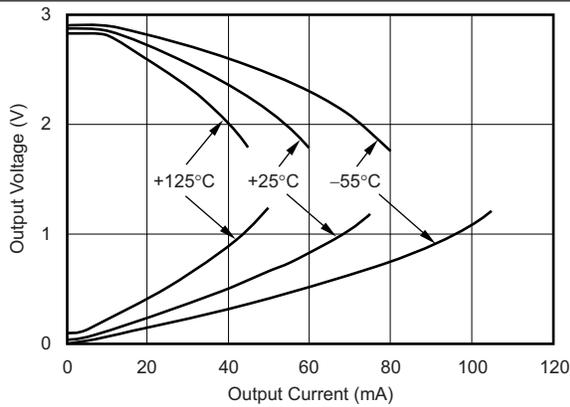
**Fig 12. Composite Video Differential Gain and Phase**



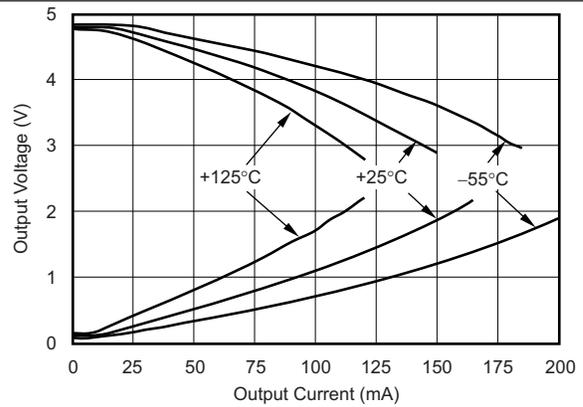
**Fig 13. Input Bias Current vs Temperature**

Typical Characteristics (continued)

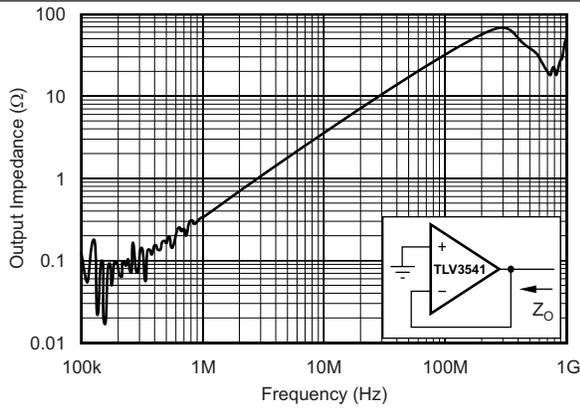
at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $G = +1$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$ , unless otherwise noted.



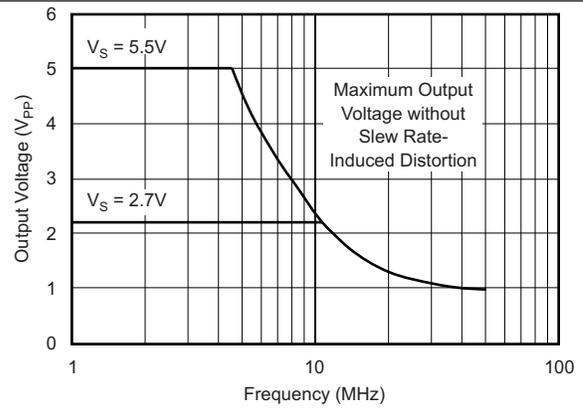
14. Output Voltage Swing vs Output Current for  $V_S = 3\text{ V}$



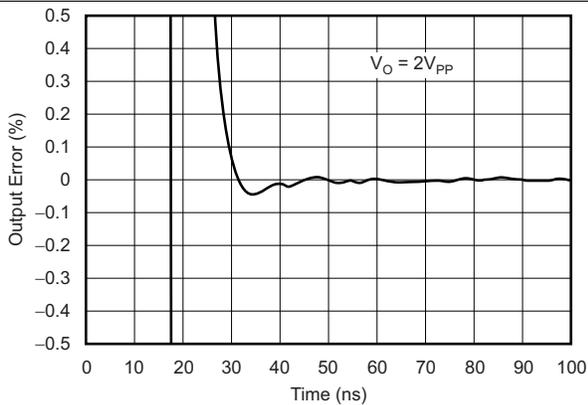
15. Output Voltage Swing vs Output Current for  $V_S = 5\text{ V}$



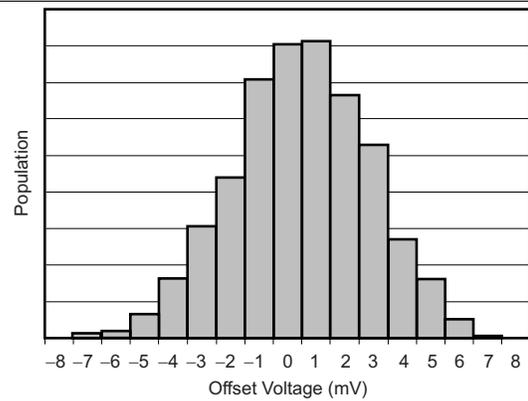
16. Closed-Loop Output Impedance vs Frequency



17. Maximum Output Voltage vs Frequency



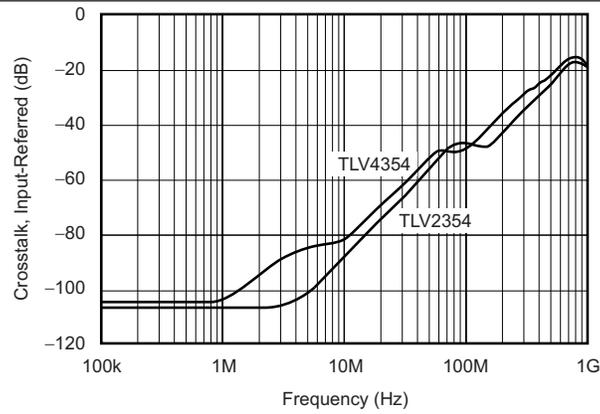
18. Output Settling Time to 0.1%



19. Offset Voltage Production Distribution

**Typical Characteristics (continued)**

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ ,  $G = +1$ ,  $R_F = 0\ \Omega$ ,  $R_L = 1\ \text{k}\Omega$ , and connected to  $V_S / 2$ , unless otherwise noted.



**20. Channel-to-Channel Crosstalk**

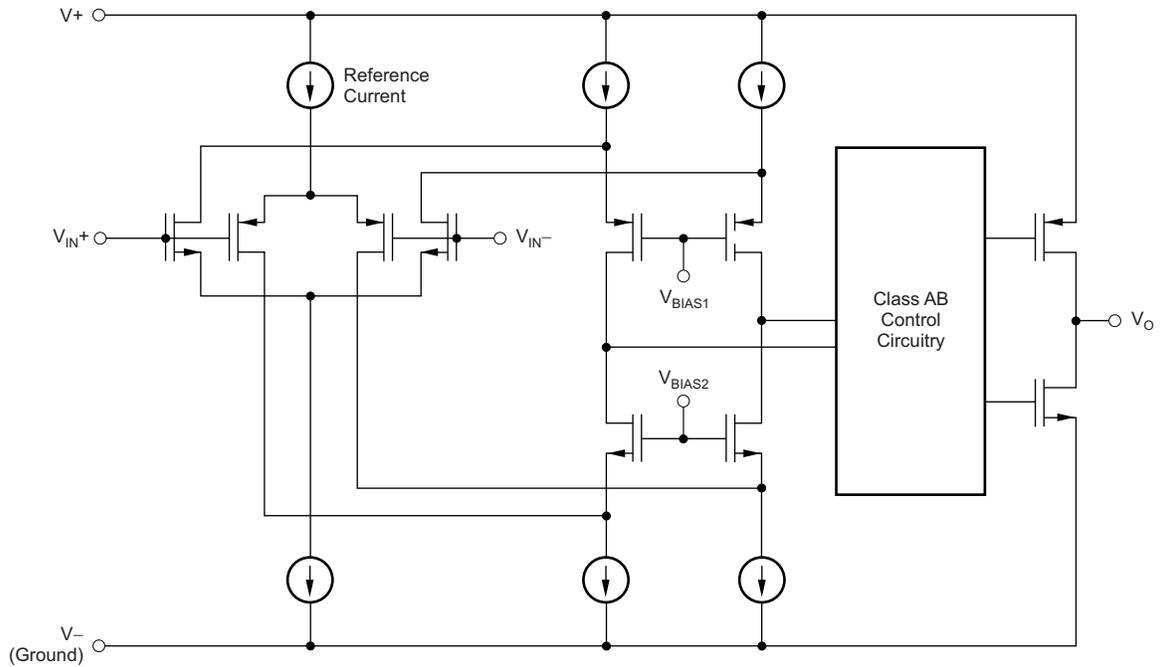
## 7 Detailed Description

### 7.1 Overview

The TLV354x is a CMOS, rail-to-rail I/O, high-speed, voltage-feedback operational amplifier designed for video, high-speed, and other applications. The device is available as a single, dual, or quad op amp.

The amplifier features a 100-MHz gain bandwidth and a 150-V/ $\mu$ s slew rate, but the amplifier is unity-gain stable and operates as a +1-V/V voltage follower.

### 7.2 Functional Block Diagram



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## 7.3 Feature Description

### 7.3.1 Operating Voltage

The TLV354x is specified over a power-supply range of 2.7 V to 5.5 V ( $\pm 1.35$  V to  $\pm 2.75$  V). However, the supply voltage may range from 2.5 V to 5.5 V ( $\pm 1.25$  V to  $\pm 2.75$  V). Supply voltages higher than 7.5 V (absolute maximum) can permanently damage the amplifier.

Parameters that vary over supply voltage or temperature are shown in the [Typical Characteristics](#) section.

### 7.3.2 Rail-to-Rail Input

The specified input common-mode voltage range of the TLV354x extends 100 mV beyond the supply rails. This extended range is achieved with a complementary input stage: an N-channel input differential pair in parallel with a P-channel differential pair, as shown in the [Functional Block Diagram](#). The N-channel pair is active for input voltages close to the positive rail, typically  $(V+) - 1.2$  V to 100 mV above the positive supply, while the P-channel pair is on for inputs from 100 mV below the negative supply to approximately  $(V+) - 1.2$  V. There is a small transition region, typically  $(V+) - 1.5$  V to  $(V+) - 0.9$  V, in which both pairs are on. This 600-mV transition region can vary  $\pm 500$  mV with process variation. Thus, the transition region (with both input stages on) can range from  $(V+) - 2.0$  V to  $(V+) - 1.5$  V on the low end, up to  $(V+) - 0.9$  V to  $(V+) - 0.4$  V on the high end.

A double-folded cascode adds the signal from the two input pairs and presents a differential signal to the class AB output stage.

### 7.3.3 Rail-to-Rail Output

A class AB output stage with common-source transistors is used to achieve rail-to-rail output. For high-impedance loads ( $> 200 \Omega$ ), the output voltage swing is typically 100 mV from the supply rails. With 10- $\Omega$  loads, a useful output swing can be achieved while maintaining high open-loop gain. See the typical characteristic curves, [Output Voltage Swing vs Output Current](#) (Figure 14 and Figure 15).

### 7.3.4 Output Drive

The TLV354x output stage can supply a continuous output current of  $\pm 100$  mA and yet provide approximately 2.7 V of output swing on a 5-V supply, as shown in Figure 21. For maximum reliability, it is not recommended to run a continuous DC current in excess of  $\pm 100$  mA. Refer to the typical characteristic curves, [Output Voltage Swing vs Output Current](#) (Figure 14 and Figure 15). For supplying continuous output currents greater than  $\pm 100$  mA, the TLV354x may be operated in parallel, as shown in Figure 22.

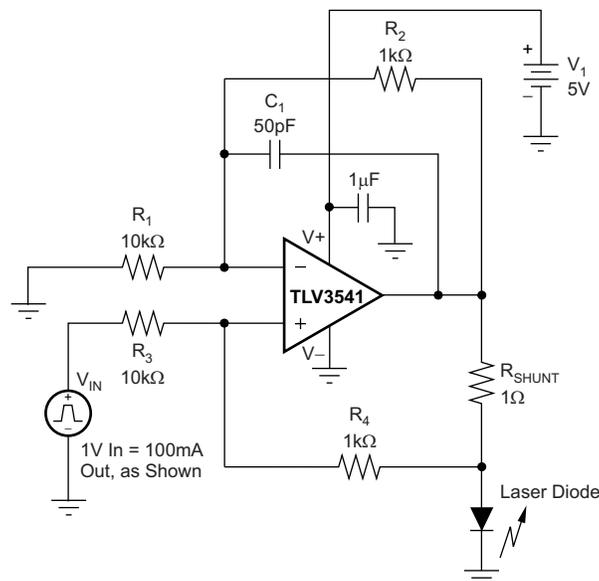
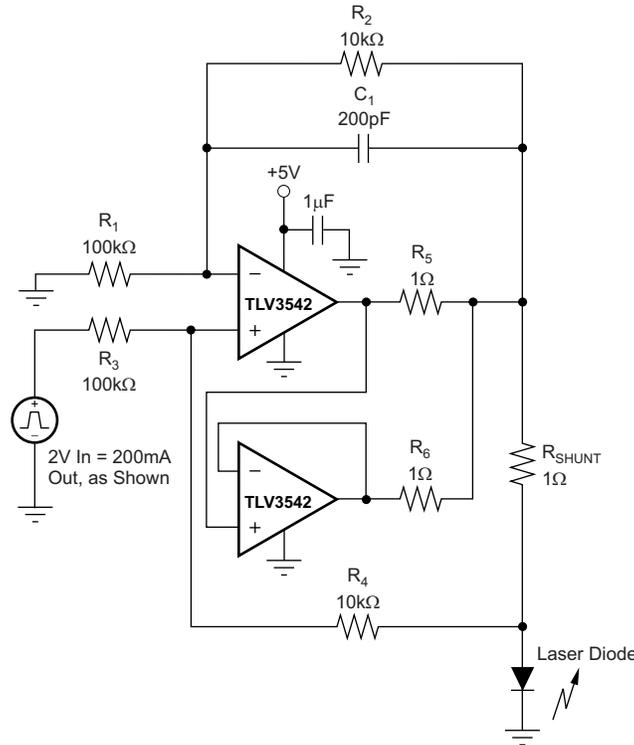


Figure 21. Laser Diode Driver

**Feature Description (continued)**

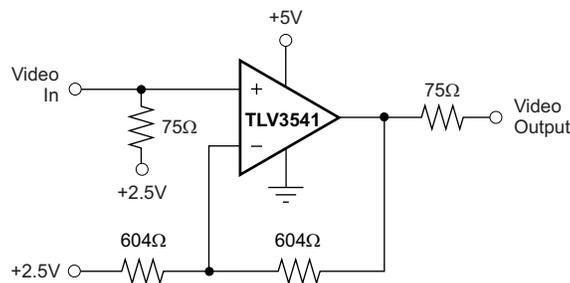
The TLV354x provides peak currents up to 200 mA, which corresponds to the typical short-circuit current. Therefore, an on-chip thermal shutdown circuit is provided to protect the TLV354x from dangerously high junction temperatures. At 160°C, the protection circuit shuts down the amplifier. Normal operation resumes when the junction temperature cools to below +140°C.



**22. Parallel Operation**

**7.3.5 Video**

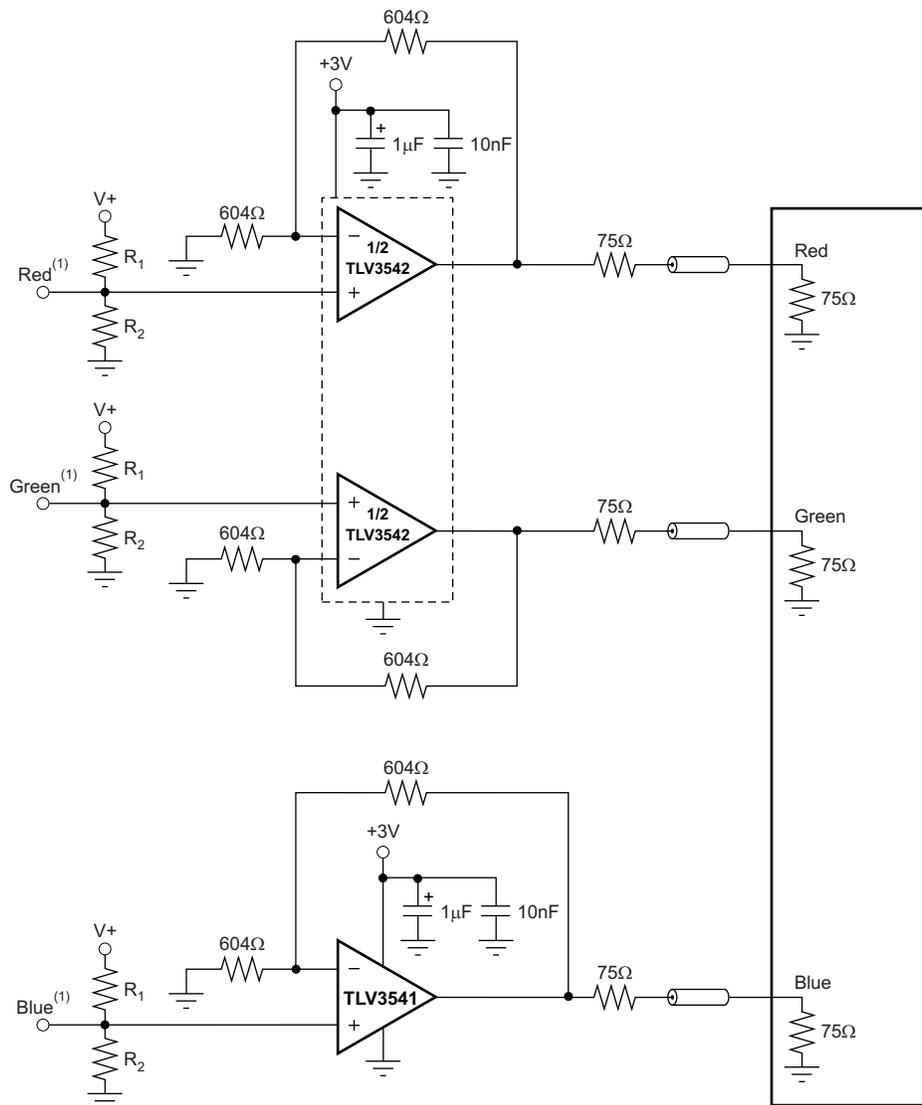
The TLV354x output stage is capable of driving standard back-terminated 75-Ω video cables, as shown in 23. By back-terminating a transmission line, the device does not exhibit a capacitive load to its driver. A properly back-terminated 75-Ω cable does not appear as capacitance; the device presents a 150-Ω resistive load to the TLV354x output.



**23. Single-Supply Video Line Driver**

The TLV3542 can be used as an amplifier for RGB graphic signals, which have a voltage of zero at the video black level, by offsetting and AC-coupling the signal. See 24.

**Feature Description (continued)**



(1) Source video signal offsets 300 mV above ground to accommodate op amp swing-to-ground capability.

**FIG 24. RGB Cable Driver**

## Feature Description (continued)

### 7.3.6 Driving Analog-to-Digital Converters

The TLV354x series op amps offer 60 ns of settling time to 0.01%, making them a good choice for driving high- and medium-speed sampling A/D converters and buffering reference circuits. The TLV354x series provide an effective means of buffering the A/D converter input capacitance and resulting charge injection while providing signal gain. For applications requiring high DC accuracy, TI recommends using the [OPA350 series](#).

Figure 25 illustrates the TLV3541 driving an A/D converter. With the TLV3541 in an inverting configuration, a capacitor across the feedback resistor can filter high-frequency noise in the signal.

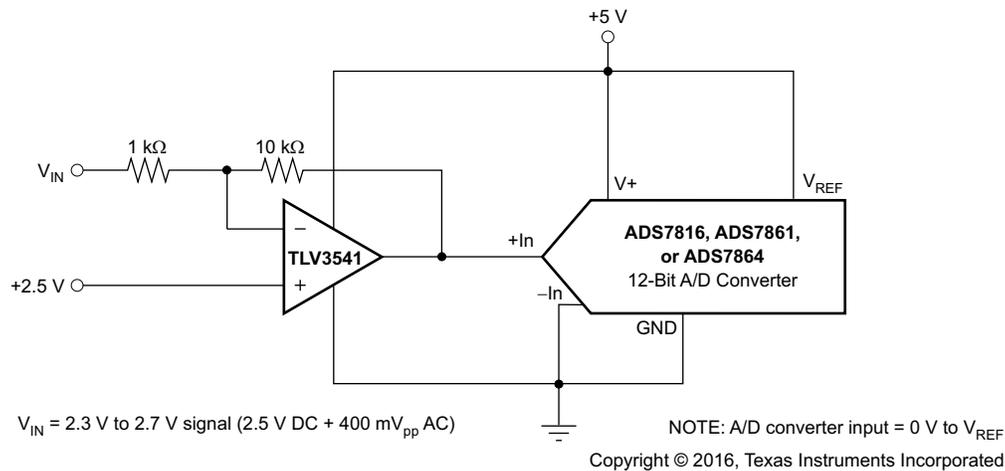


Figure 25. The TLV3541 in Inverting Configuration Driving the ADS7816

### 7.3.7 Capacitive Load and Stability

The TLV354x series op amps can drive a wide range of capacitive loads. However, all op amps under certain conditions may become unstable. Op amp configuration, gain, and load value are just a few of the factors to consider when determining stability. An op amp in unity-gain configuration is most susceptible to the effects of capacitive loading. The capacitive load reacts with the device output resistance, along with any additional load resistance, to create a pole in the small-signal response that degrades the phase margin. Refer to the typical characteristic curve, *Frequency Response for Various  $C_L$*  (Figure 7) for details.

The TLV354x topology enhances the ability to drive capacitive loads. In unity gain, these op amps perform well with large capacitive loads. Refer to the typical characteristic curves, *Recommended  $R_S$  vs Capacitive Load* (Figure 8) and *Frequency Response vs Capacitive Load* (Figure 9) for details.

One method of improving capacitive load drive in the unity-gain configuration is to insert a 10- $\Omega$  to 20- $\Omega$  resistor in series with the output, as shown in Figure 26. This configuration significantly reduces ringing with large capacitive loads. See the typical characteristic curve, *Frequency Response vs Capacitive Load* (Figure 9). However, if there is a resistive load in parallel with the capacitive load,  $R_S$  creates a voltage divider. This voltage division introduces a DC error at the output and slightly reduces output swing. This error may be insignificant. For instance, with  $R_L = 10\text{ k}\Omega$  and  $R_S = 20\ \Omega$ , there is an error of approximately 0.2% at the output.

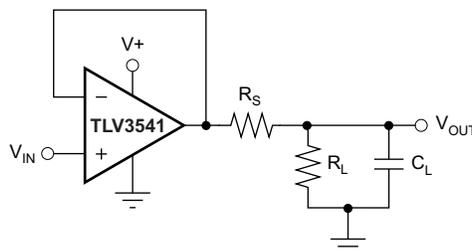


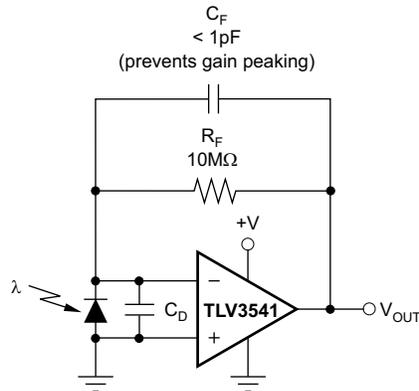
Figure 26. Series Resistor in Unity-Gain Configuration Improves Capacitive Load Drive

## Feature Description (continued)

### 7.3.8 Wideband Transimpedance Amplifier

Wide bandwidth, low input bias current, and low input voltage and current noise make the TLV354x a suitable wideband photodiode transimpedance amplifier for low-voltage, single-supply applications. Low-voltage noise is important because photodiode capacitance causes the effective noise gain of the circuit to increase at high frequency.

The key elements to a transimpedance design, as shown in [Figure 27](#), are the expected diode capacitance (including the parasitic input common-mode and differential-mode input capacitance (2 + 2) pF for the TLV354x), the desired transimpedance gain ( $R_F$ ), and the Gain-Bandwidth Product (GBW) for the TLV354x (100 MHz, typical). With these three variables set, the feedback capacitor value ( $C_F$ ) may be set to control the frequency response.



**Figure 27. Transimpedance Amplifier**

To achieve a flat, second-order, Butterworth frequency response, the feedback pole must be set as shown in [Equation 1](#):

$$\frac{1}{2\pi R_F C_F} = \sqrt{\frac{\text{GBP}}{4\pi R_F C_D}} \quad (1)$$

Typical surface-mount resistors have a parasitic capacitance of approximately 0.2 pF that must be deducted from the calculated feedback capacitance value. Bandwidth is calculated by [Equation 2](#):

$$f_{-3\text{dB}} = \sqrt{\frac{\text{GBP}}{2\pi R_F C_D}} \text{ Hz} \quad (2)$$

For even higher transimpedance bandwidth, the high-speed CMOS [OPA355](#) (200-MHz GBW) or the [OPA655](#) (400-MHz GBW) may be used.

## 7.4 Device Functional Modes

The TLV354x has dual functional modes and is operational when the power-supply voltage is greater than 2.5 V ( $\pm 1.25$  V). The maximum power-supply voltage for the TLV354x is 5.5 V ( $\pm 2.75$  V). At +160°C, the protection circuit shuts down the amplifier. Normal operation resumes when the junction temperature cools to below +140°C.

## 8 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

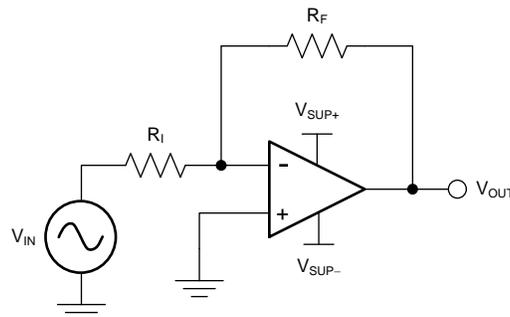
### 8.1 Application Information

The TLV354x are wide bandwidth, low-noise, rail-to-rail input and output amplifiers. These devices operate from 2.5 V to 5.5 V, are unity-gain stable, and suitable for a wide range of general-purpose applications. The input common-mode voltage range includes both rails, and allows the TLV354x device to be used in any single-supply application. Rail-to-rail input and output swing significantly increases dynamic range, especially in low-supply applications, and makes the device ideal for driving analog-to-digital converters (ADCs).

The TLV354x family of devices features a 200-MHz bandwidth and 150-V/ $\mu$ s slew rate with only 7.5 nV/ $\sqrt{\text{Hz}}$  of broadband noise.

### 8.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in [Figure 28](#). An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier makes negative input voltages positive on the output. In addition, amplification can be added by selecting the input resistor  $R_I$  and the feedback resistor  $R_F$ .



**Figure 28. Application Schematic**

#### 8.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range ( $V_{CM}$ ) and the output voltage swing to the rails ( $V_O$ ) must be considered. For instance, this application scales a signal of  $\pm 0.5$  V (1 V) to  $\pm 1.8$  V (3.6 V). Setting the supply at  $\pm 2.5$  V is sufficient to accommodate this application.

#### 8.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using [Equation 3](#) and [Equation 4](#):

$$A_V = \frac{V_{OUT}}{V_{IN}} \tag{3}$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \tag{4}$$

### Typical Application (continued)

When the desired gain is determined, select a value for  $R_I$  or  $R_F$ . Selecting a value in the kilo ohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures the device does not draw too much current. The trade-off is that large resistors (100s of kilo ohms) draw the smallest current but generate the highest noise. Small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k $\Omega$  for  $R_I$ , meaning 36 k $\Omega$  is used for  $R_F$ . These values are determined by 式 5:

$$A_V = -\frac{R_F}{R_I} \tag{5}$$

### 8.2.3 Application Curve

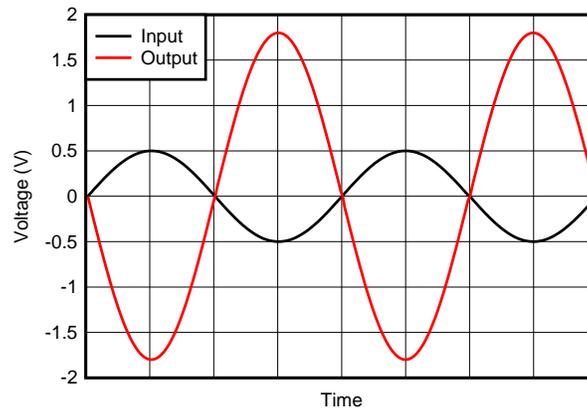
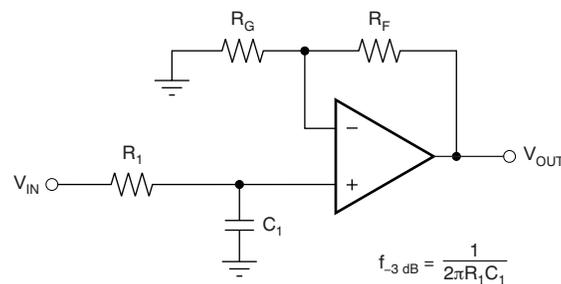


图 29. Inverting Amplifier Input and Output

### 8.3 System Examples

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to establish this limited bandwidth is to place an RC filter at the noninverting terminal of the amplifier, as shown in 图 30.



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1C_1}\right)$$

图 30. Single-Pole, Low-Pass Filter

## System Examples (continued)

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter can be used for this task, as shown in [Figure 31](#). For best results, the amplifier must have a bandwidth that is eight to ten times the filter frequency bandwidth. Failure to follow this guideline can result in phase shift of the amplifier.

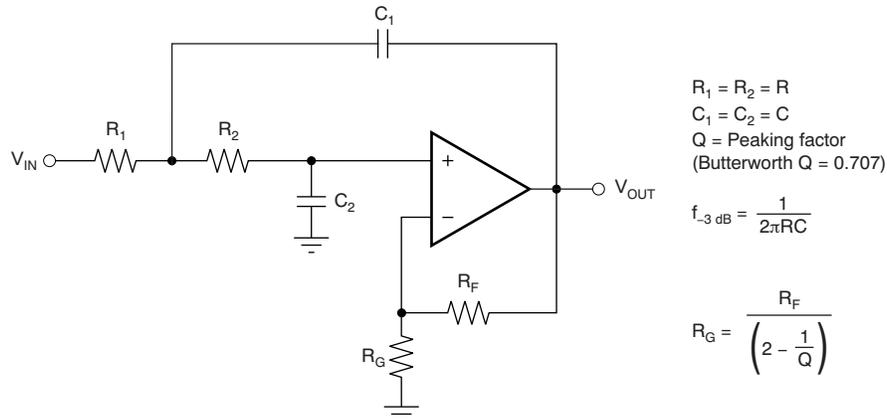


Figure 31. Two-Pole, Low-Pass, Sallen-Key Filter

## 9 Power Supply Recommendations

The TLV354x family is specified from 2.7 V to 5.5 V ( $\pm 1.35$  V to  $\pm 2.75$  V), although the devices can operate from 2.5 V to 5.5 V ( $\pm 1.25$  V to  $\pm 2.75$  V); many specifications apply from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . [Typical Characteristics](#) presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

### 注意

Supply voltages larger than 7.5 V can permanently damage the device. (See the *Absolute Maximum Ratings* table).

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see [Layout Guidelines](#).

### 9.1 Input and ESD Protection

The TLV354x family incorporates internal electrostatic discharge (ESD) protection circuits on all pins. In the case of input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA, as stated in the *Absolute Maximum Ratings* table. [Figure 32](#) shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input, which must be kept to a minimum in noise-sensitive applications.

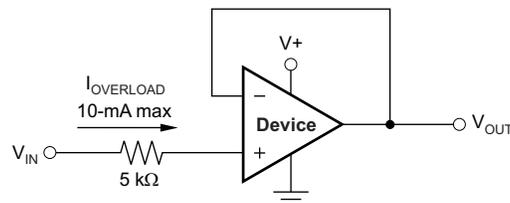


Figure 32. Input Current Protection

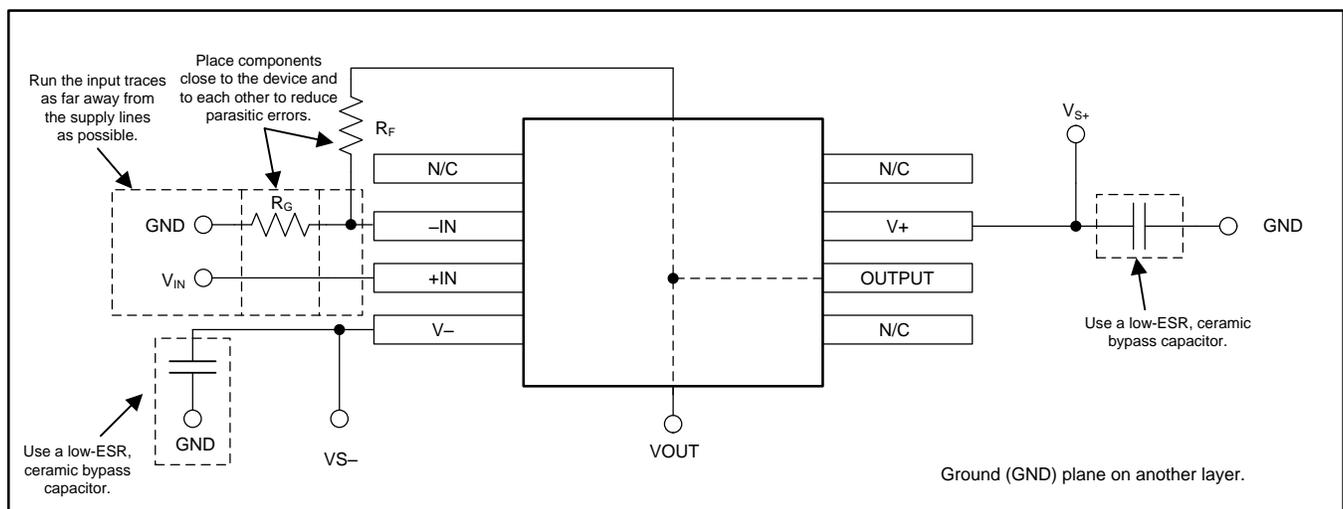
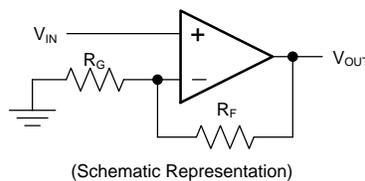
## 10 Layout

### 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise propagates into analog circuitry through the power pins of the circuit as a whole and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu$ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are typically devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep  $R_F$  and  $R_G$  close to the inverting input to minimize parasitic capacitance, as shown in [Figure 33](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

### 10.2 Layout Example



**Figure 33. Operational Amplifier Board Layout for Noninverting Configuration**

## 11 デバイスおよびドキュメントのサポート

### 11.1 ドキュメントのサポート

#### 11.1.1 関連資料

TLV354xデバイスについて、以下の参照資料の使用をお勧めします。すべてのドキュメントは、特に記述のない限り [www.ti.com](http://www.ti.com) からダウンロードできます。

- 『オペアンプ・アプリケーション・ハンドブック』(SBOA092)
- 『アナログ・エンジニアのためのポケット・リファレンス』(SLYW038)

#### 11.2 関連リンク

表 1 に、クイック・アクセス・リンクの一覧を示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびサンプル注文またはご購入へのクイック・アクセスが含まれます。

表 1. 関連リンク

製品	プロダクト・フォルダ	サンプルとご購入	技術資料	ツールとソフトウェア	サポートとコミュニティ
TLV3541	<a href="#">ここをクリック</a>				
TLV3542	<a href="#">ここをクリック</a>				
TLV3544	<a href="#">ここをクリック</a>				

#### 11.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](http://ti.com) のデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

#### 11.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.5 商標

E2E is a trademark of Texas Instruments.  
All other trademarks are the property of their respective owners.

#### 11.6 静電気放電に関する注意事項



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#### 11.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

**PACKAGING INFORMATION**

Orderable part number	Status (1)	Material type (2)	Package   Pins	Package qty   Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
<a href="#">TLV3541IDBVR</a>	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVR.A	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVR.B	Active	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVRG4	Last Time Buy	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVRG4.A	Last Time Buy	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVRG4.B	Last Time Buy	Production	SOT-23 (DBV)   5	3000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
<a href="#">TLV3541IDBVT</a>	Active	Production	SOT-23 (DBV)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
TLV3541IDBVT.B	Active	Production	SOT-23 (DBV)   5	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	17MD
<a href="#">TLV3541IDR</a>	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3541
TLV3541IDR.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3541
TLV3541IDR.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3541
<a href="#">TLV3542IDGKR</a>	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU   SN   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	18TE
TLV3542IDGKR.B	Active	Production	VSSOP (DGK)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	18TE
<a href="#">TLV3542IDGKT</a>	Active	Production	VSSOP (DGK)   8	250   SMALL T&R	Yes	NIPDAU   SN   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	18TE
TLV3542IDGKT.B	Active	Production	VSSOP (DGK)   8	250   SMALL T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	18TE
<a href="#">TLV3542IDR</a>	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3542
TLV3542IDR.A	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3542
TLV3542IDR.B	Active	Production	SOIC (D)   8	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL3542
<a href="#">TLV3544IDR</a>	Active	Production	SOIC (D)   14	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV3544A
TLV3544IDR.B	Active	Production	SOIC (D)   14	2500   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV3544A
<a href="#">TLV3544IPWR</a>	Active	Production	TSSOP (PW)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV 3544
TLV3544IPWR.B	Active	Production	TSSOP (PW)   14	2000   LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TLV 3544

(1) **Status:** For more details on status, see our [product life cycle](#).

- (2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.
- (3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.
- (4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.
- (5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.
- (6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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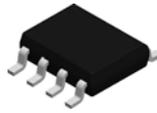
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF TLV3544 :**

- Automotive : [TLV3544-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

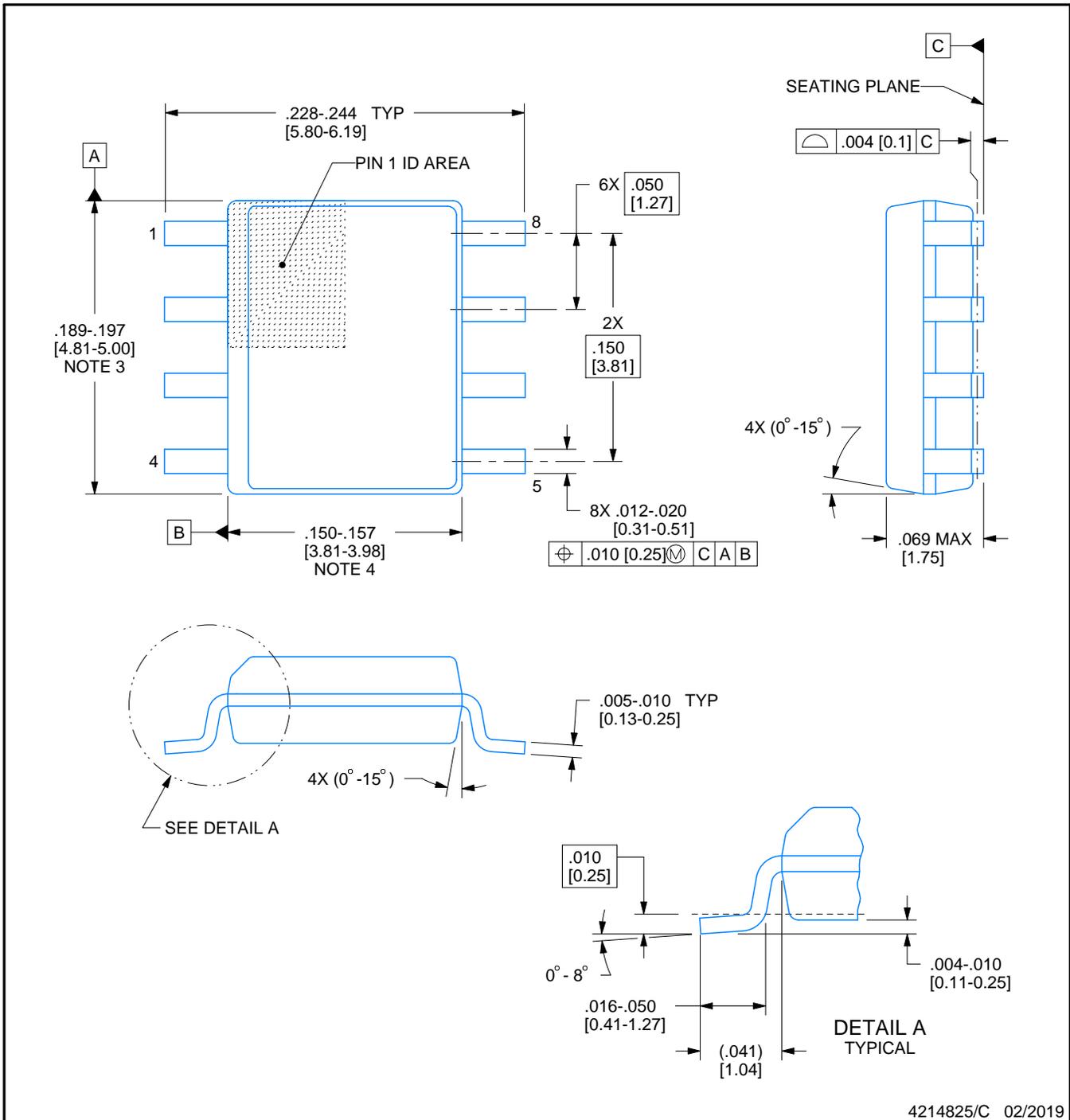


D0008A

# PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

### NOTES:

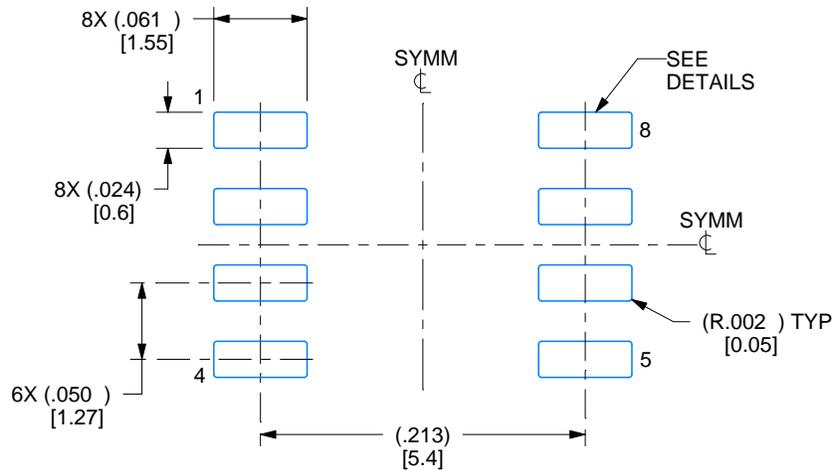
- Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed  $.006$  [0.15] per side.
- This dimension does not include interlead flash.
- Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

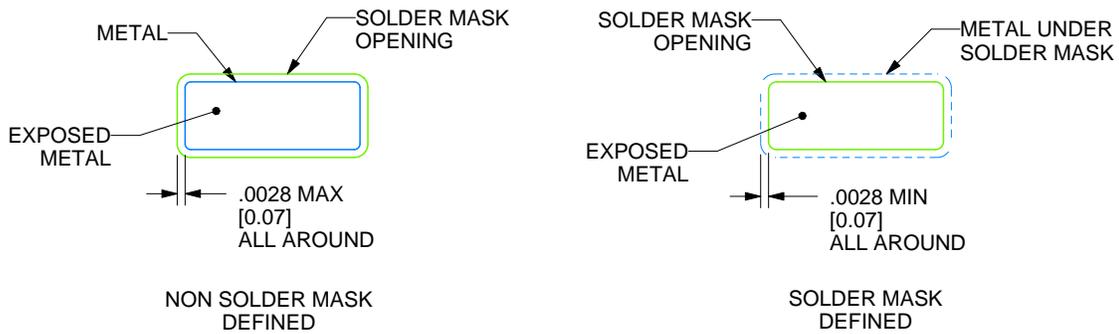
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

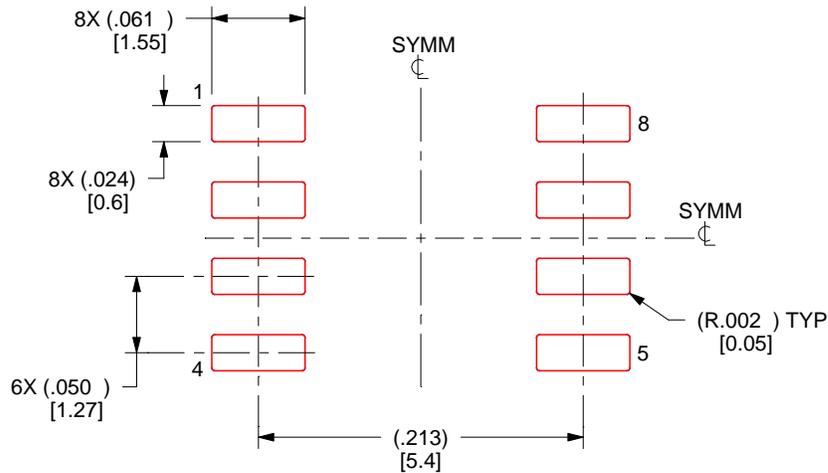
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

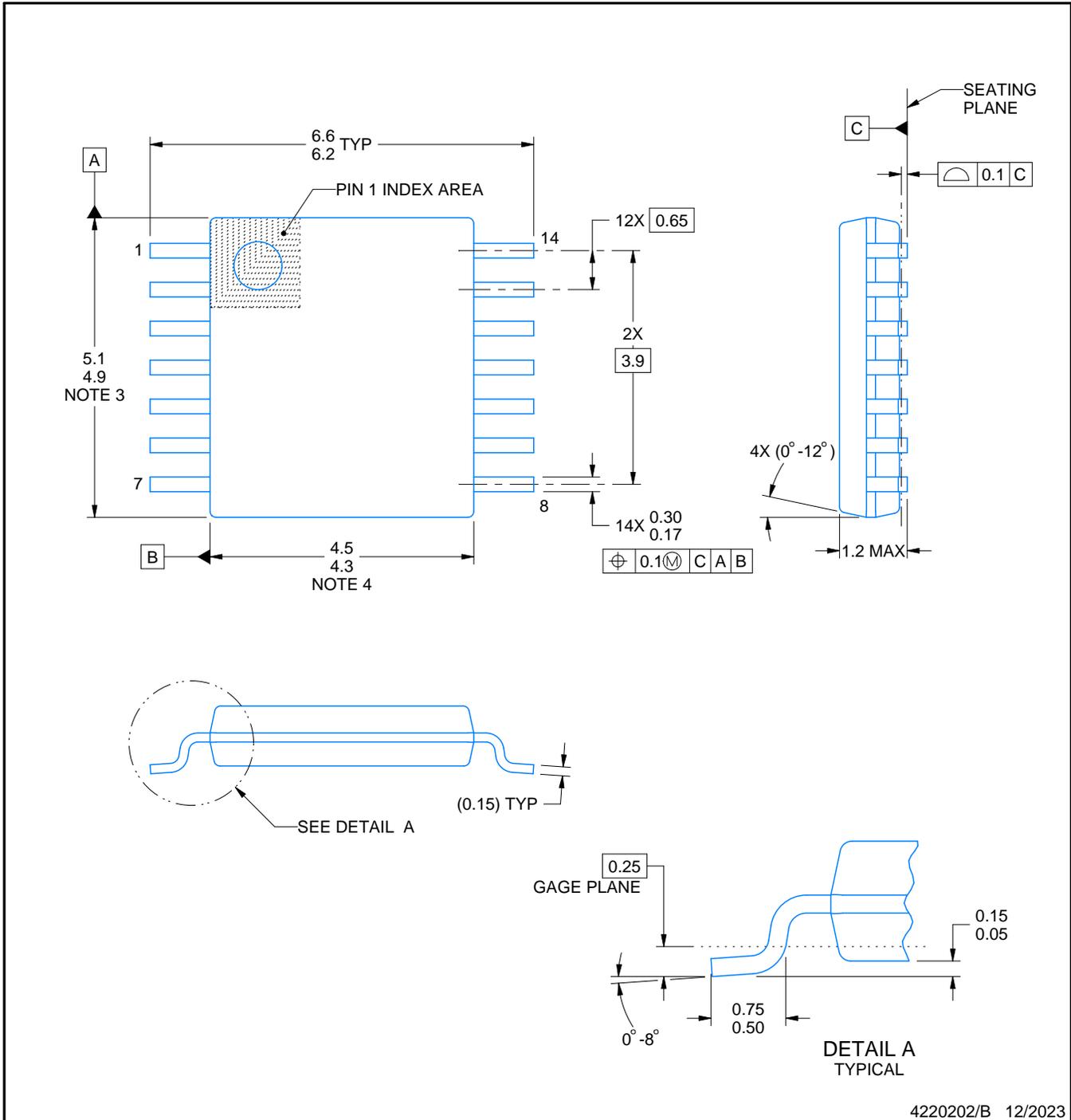
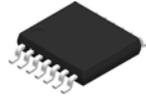


SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220202/B 12/2023

NOTES:

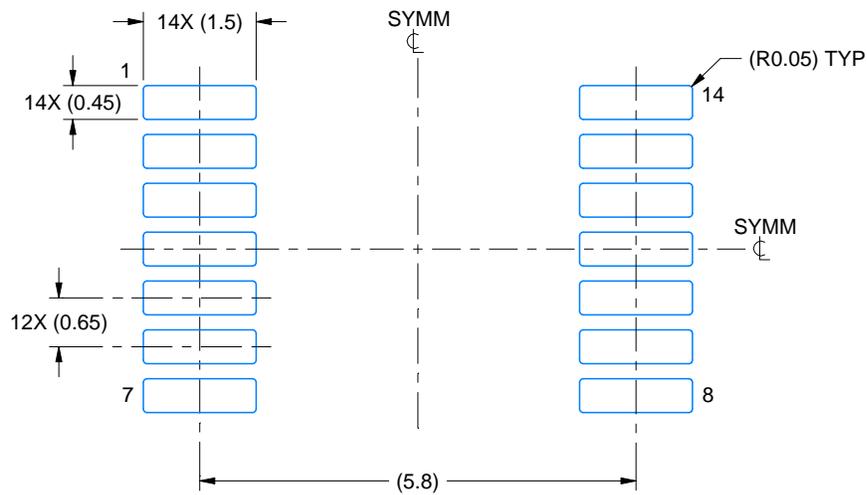
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

# EXAMPLE BOARD LAYOUT

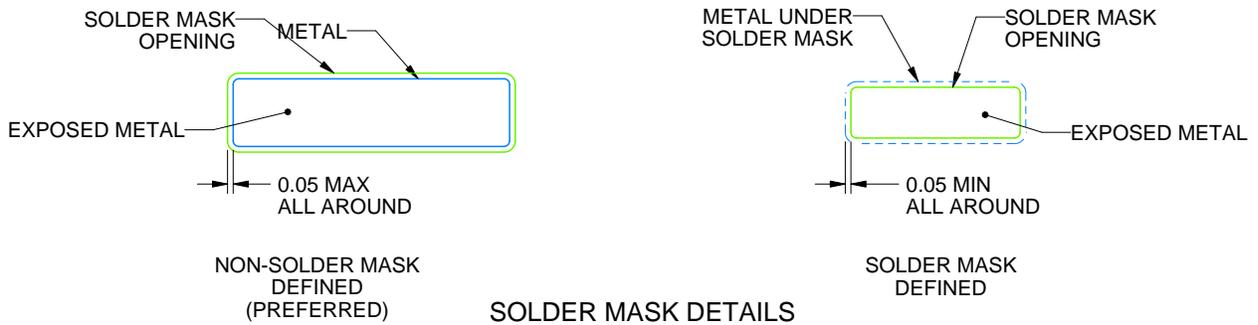
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



4220202/B 12/2023

NOTES: (continued)

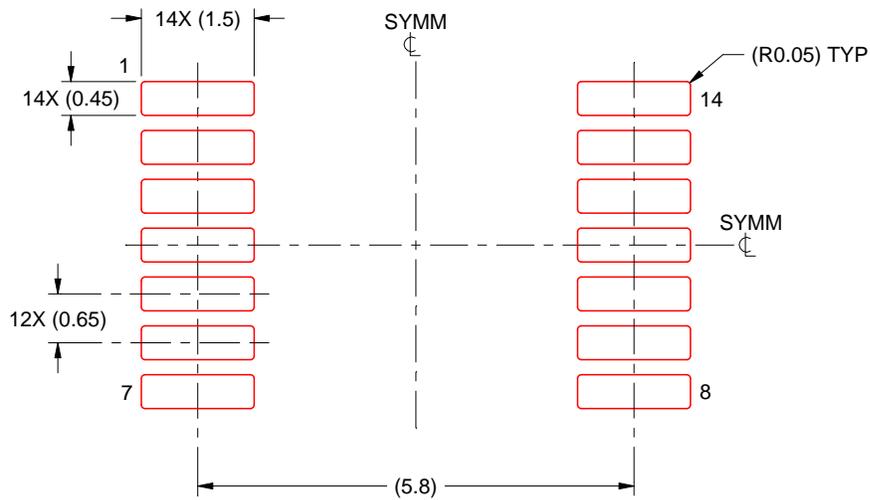
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

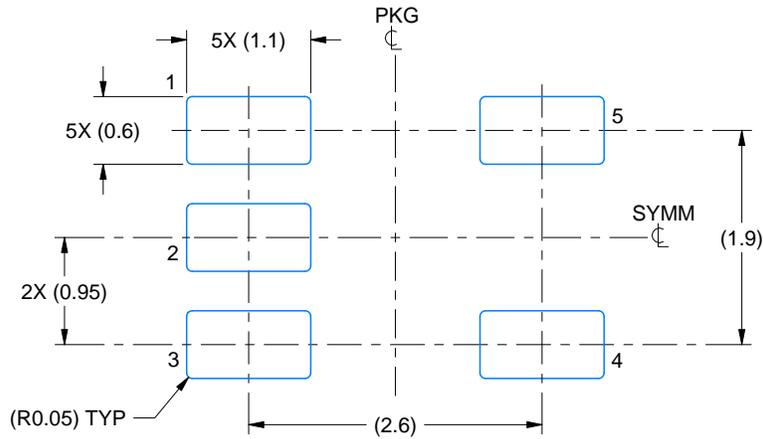


# EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

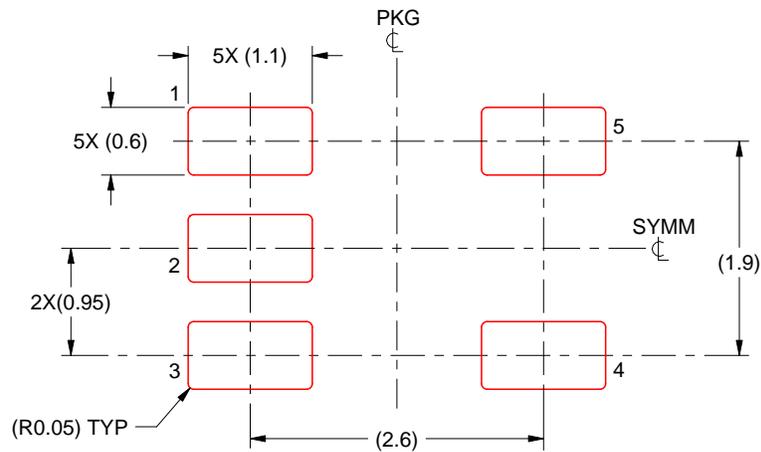
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

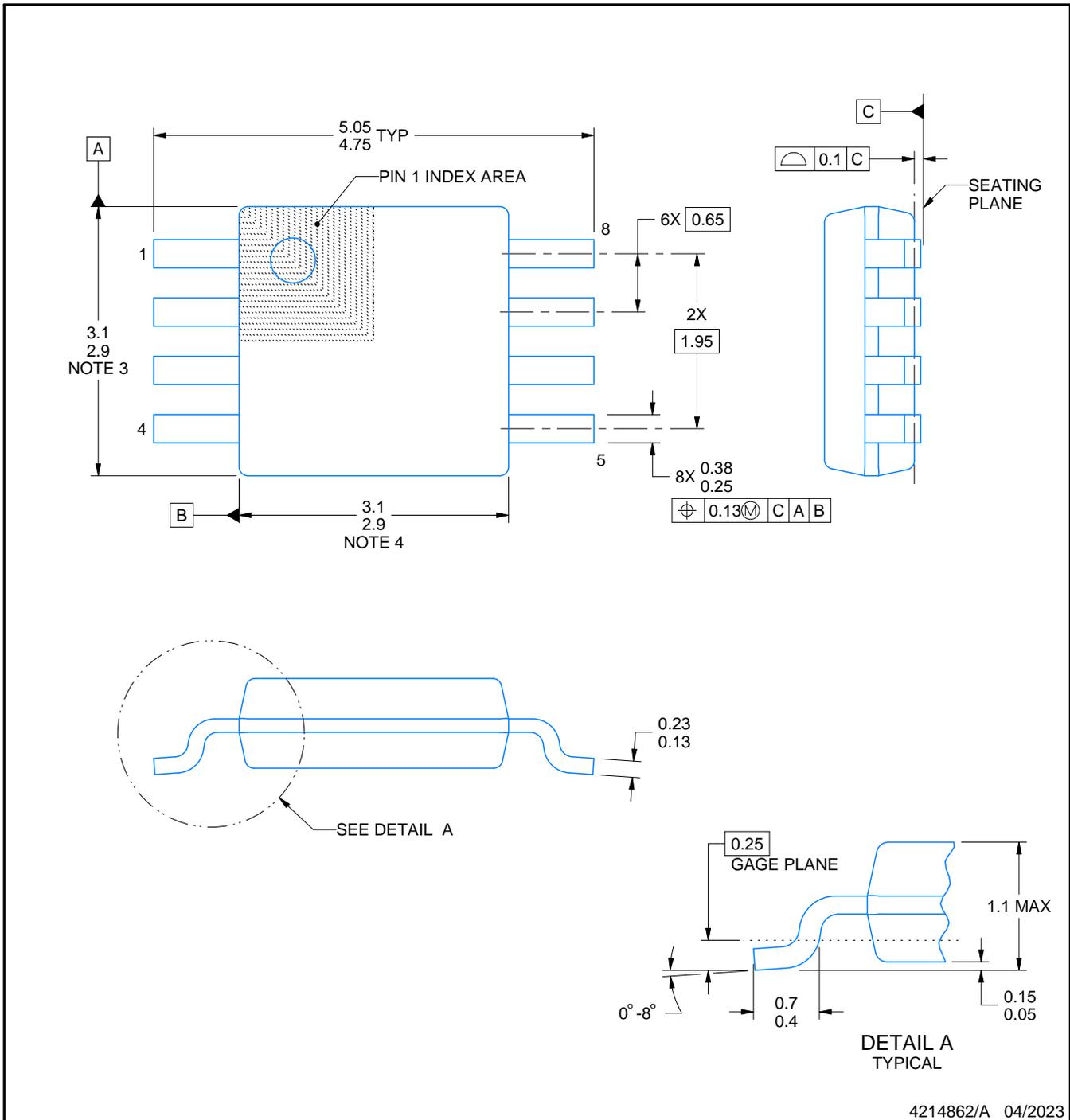
# DGK0008A



# PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

**NOTES:**

PowerPAD is a trademark of Texas Instruments.

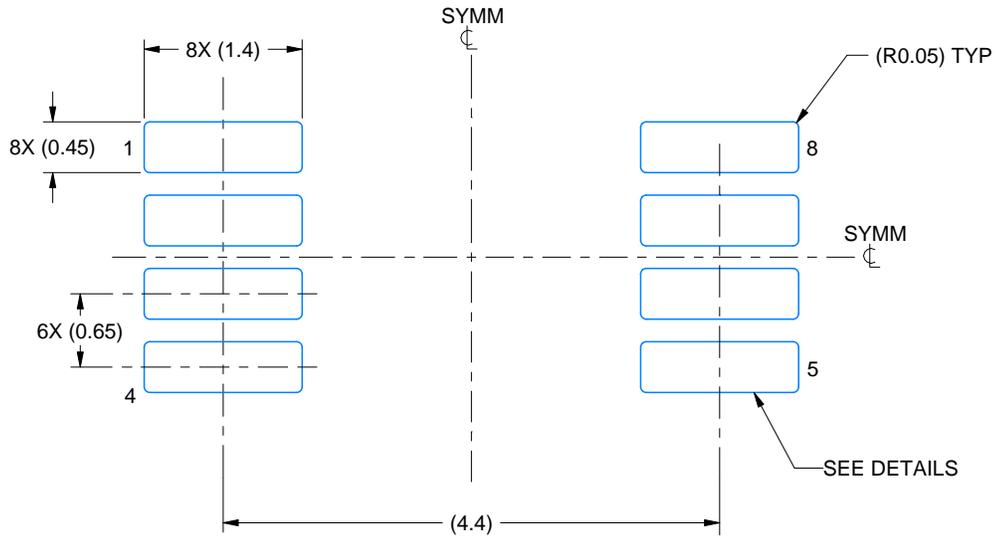
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

# EXAMPLE BOARD LAYOUT

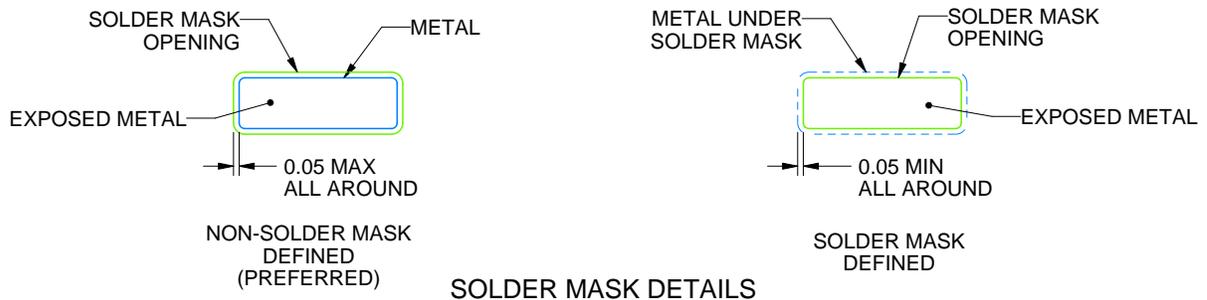
DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

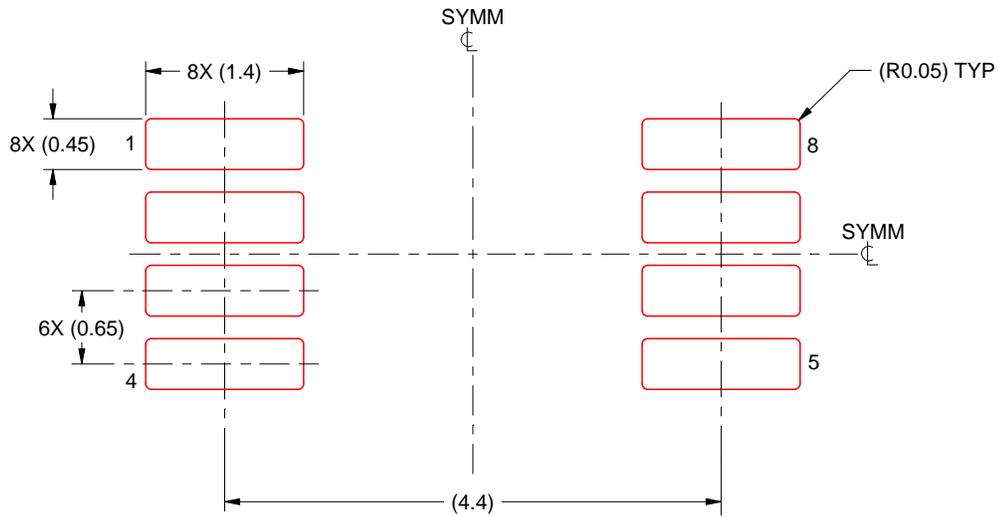
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

# EXAMPLE STENCIL DESIGN

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

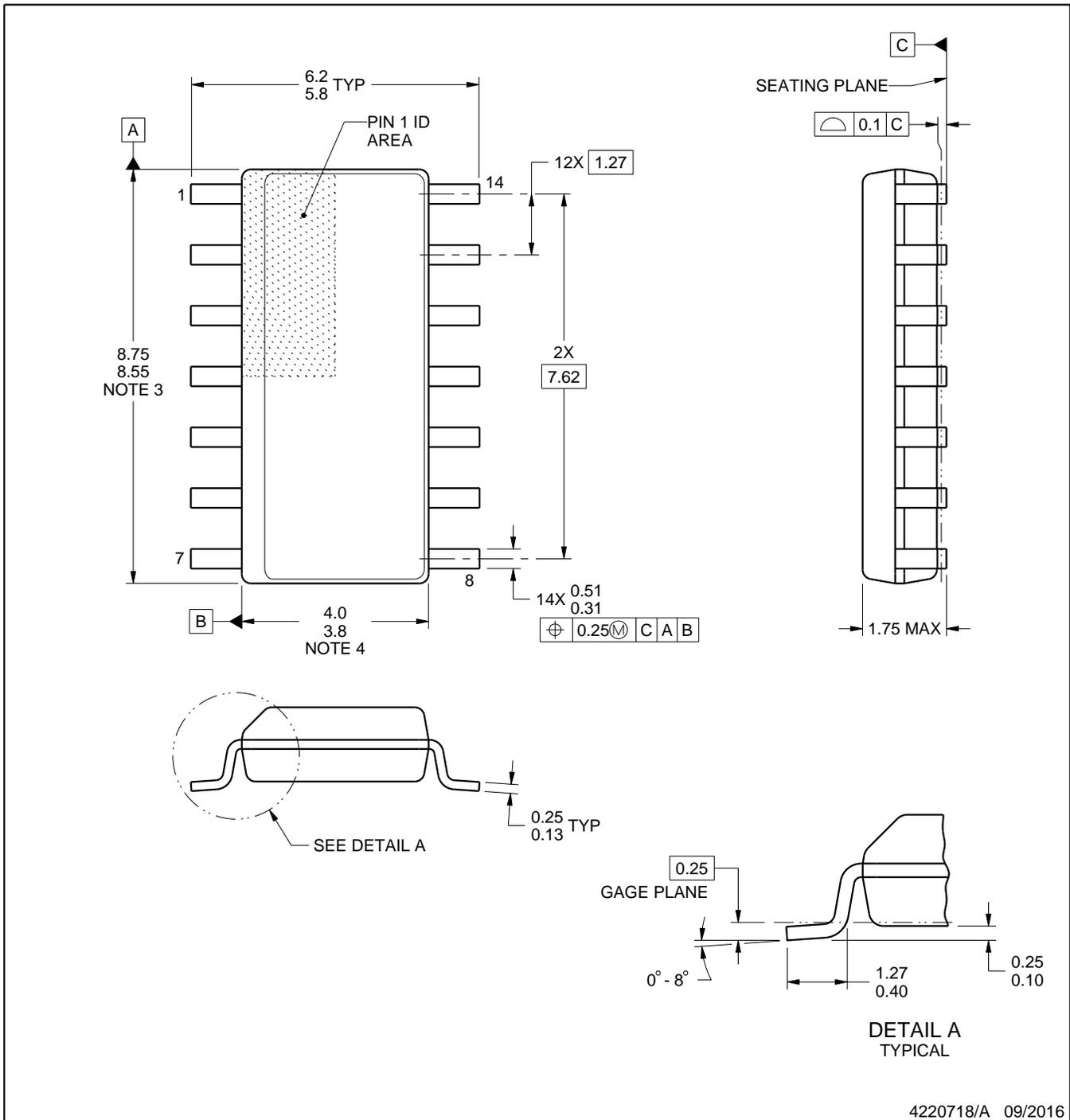
D0014A



# PACKAGE OUTLINE

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

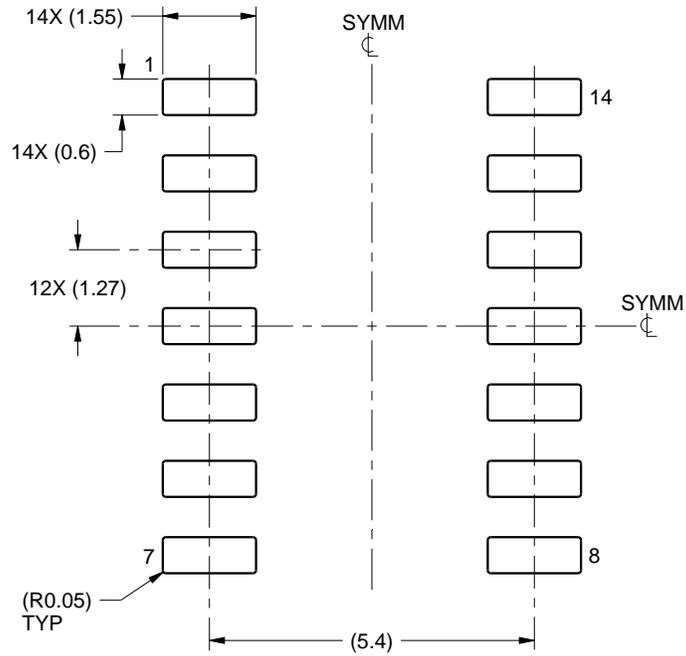
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

# EXAMPLE BOARD LAYOUT

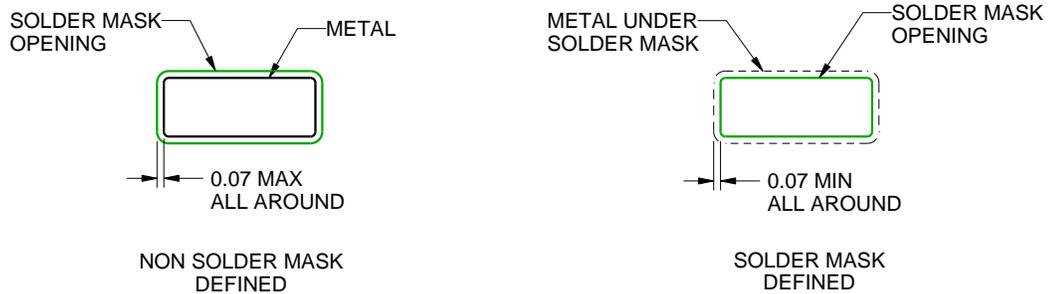
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

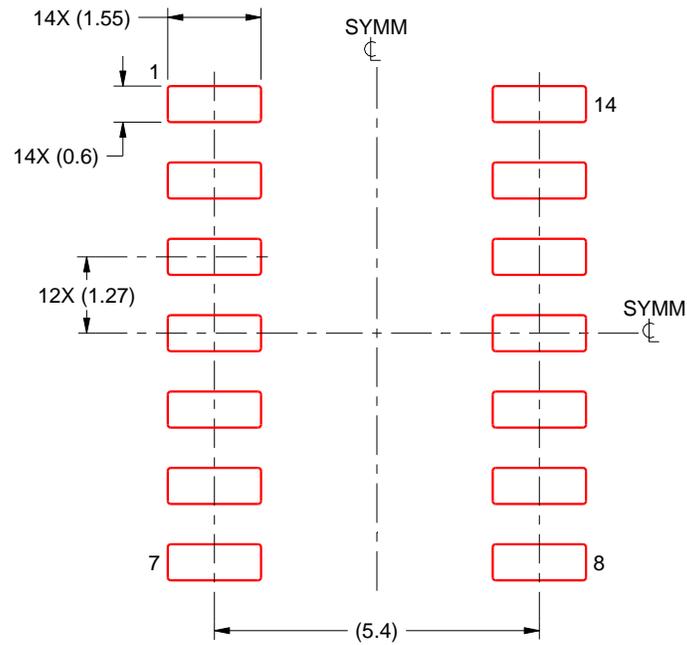
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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最終更新日 : 2025 年 10 月